Complementary Power Transistors

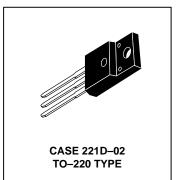
For Isolated Package Applications

Designed for general-purpose amplifier and switching applications, where the mounting surface of the device is required to be electrically isolated from the heatsink or chassis.

- Electrically Similar to the Popular MJE15030 and MJE15031
- 150 VCEO(sus)
- 8 A Rated Collector Current
- · No Isolating Washers Required
- Reduced System Cost
- High Current Gain–Bandwidth Product
 fT = 30 MHz (Min) @ IC = 500 mAdc
- UL Recognized, File #E69369, to 3500 V_{RMS} Isolation

MJF15030 PNP MJF15031

COMPLEMENTARY
SILICON
POWER TRANSISTORS
8 AMPERES
150 VOLTS
36 WATTS



MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector–Emitter Voltage		VCEO	150	Vdc
Collector-Base Voltage		V _{CB}	150	Vdc
Emitter–Base Voltage		V _{EB}	5	Vdc
RMS Isolation Voltage (1) (for 1 sec, R.H. < 30%, T _A = 25°C)	Test No. 1 Per Fig. 11 Test No. 2 Per Fig. 12 Test No. 3 Per Fig. 13	VISOL	4500 3500 1500	V _{RMS}
Collector Current — Continuous — Peak		lc	8 16	Adc
Base Current		ΙΒ	2	Adc
Total Power Dissipation* @ T _C = 25°C Derate above 25°C		P _D	36 0.29	Watts W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C		P _D	2 0.016	Watts W/°C
Operating and Storage Junction Temperature Range		TJ, T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic		Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction to Case*	$R_{\theta JC}$	3.5	°C/W
Lead Temperature for Soldering Purpose	TL	260	°C

^{*} Measurement made with thermocouple contacting the bottom insulated mounting surface (in a location beneath the die), the device mounted on a heatsink with thermal grease and a mounting torque of ≥ 6 in. lbs.



⁽¹⁾ Proper strike and creepage distance must be provided.

MJF15030 MJF15031

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) (I _C = 10 mAdc, I _B = 0)	VCEO(sus)	150	-	Vdc
Collector Cutoff Current (V _{CE} = 150 Vdc, I _B = 0)		_	10	μAdc
Collector Cutoff Current (V _{CB} = 150 Vdc, I _E = 0)		_	10	μAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	_	10	μAdc
ON CHARACTERISTICS (1)				
DC Current Gain ($I_C = 0.1$ Adc, $V_{CE} = 2$ Vdc) ($I_C = 2$ Adc, $V_{CE} = 2$ Vdc) ($I_C = 3$ Adc, $V_{CE} = 2$ Vdc) ($I_C = 4$ Adc, $V_{CE} = 2$ Vdc)	hFE	40 40 40 20	_ _ _ _	_
DC Current Gain Linearity (VCE from 2 V to 20 V, IC from 0.1 A to 3 A) (NPN to PNP)	hFE	Typ 2 3		
Collector–Emitter Saturation Voltage (I _C = 1 Adc, I _B = 0.1 Adc)		_	0.5	Vdc
Base–Emitter On Voltage (I _C = 1 Adc, V _{CE} = 2 Vdc)	V _{BE(on)}		1	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain–Bandwidth Product (2) (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 10 MHz)	fΤ	30	_	MHz

NOTES:

- 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 2. $f_T = |h_{fe}| \cdot f_{test}$.

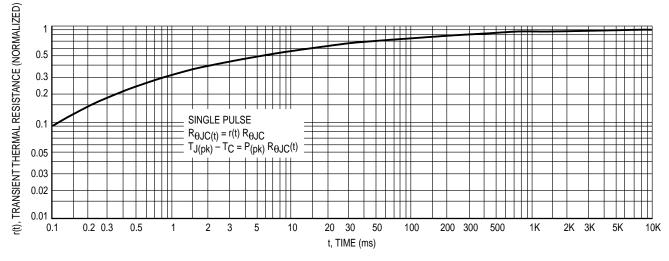


Figure 1. Thermal Response

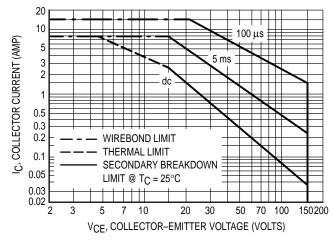


Figure 2. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 2 and 3 is based on $T_{J(pk)} = 150\,^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150\,^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJF15030 MJF15031

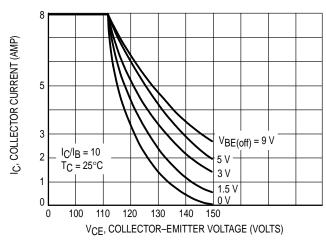


Figure 3. Reverse Bias Switching Safe Operating Area

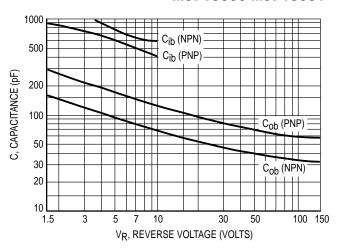


Figure 4. Capacitances

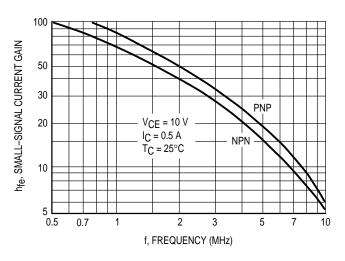


Figure 5. Small-Signal Current Gain

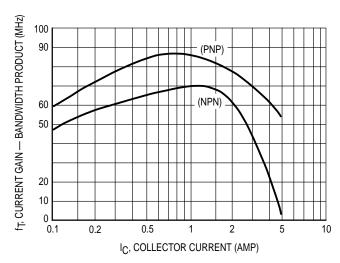


Figure 6. Current Gain — Bandwidth Product

DC CURRENT GAIN

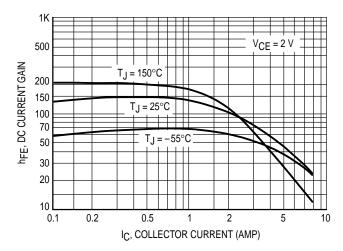


Figure 7a. MJF15030 NPN

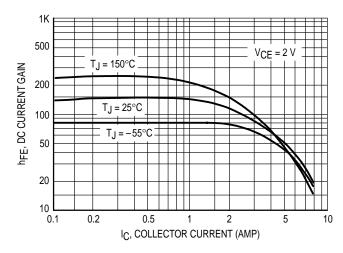


Figure 7b. MJF15031 PNP

"ON" VOLTAGE

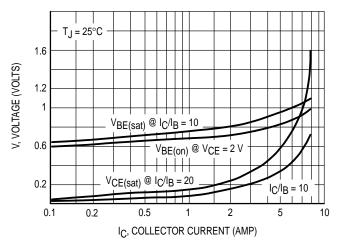


Figure 8a. MJF15030 NPN

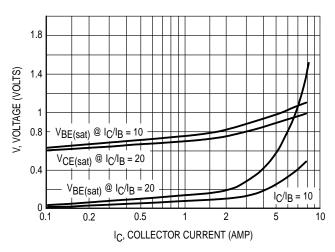


Figure 8b. MJF15031 PNP

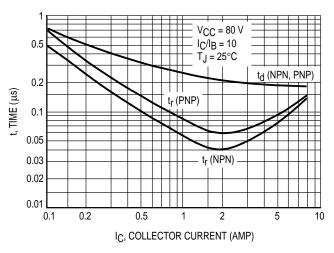


Figure 9. Turn-On Times

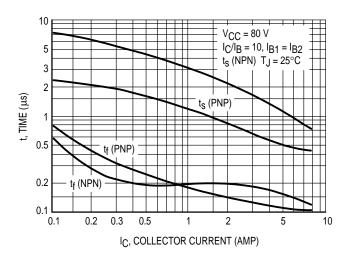
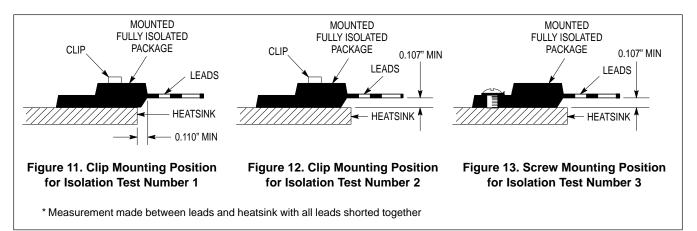


Figure 10. Turn-Off Times

TEST CONDITIONS FOR ISOLATION TESTS*



MOUNTING INFORMATION

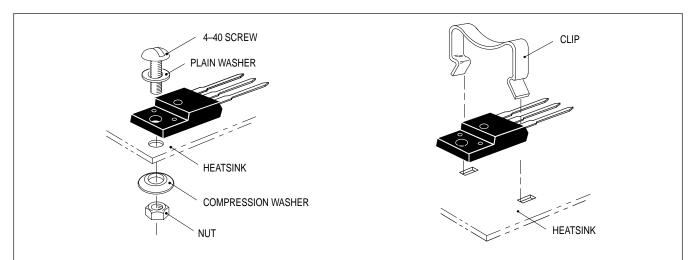


Figure 14. Typical Mounting Techniques*

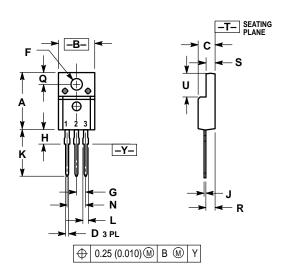
Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4–40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4–40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, Motorola does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

^{**} For more information about mounting power semiconductors see Application Note AN1040.

PACKAGE DIMENSIONS



- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.621	0.629	15.78	15.97	
В	0.394	0.402	10.01	10.21	
С	0.181	0.189	4.60	4.80	
D	0.026	0.034	0.67	0.86	
F	0.121	0.129	3.08	3.27	
G	0.100	0.100 BSC		2.54 BSC	
Н	0.123	0.129	3.13	3.27	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.14	1.52	
N	0.200	BSC	5.08	5.08 BSC	
Q	0.126	0.134	3.21	3.40	
R	0.107	0.111	2.72	2.81	
S	0.096	0.104	2.44	2.64	
U	0.259	0.267	6.58	6.78	

STYLE 2:

PIN 1. BASE

- COLLECTOR EMITTER

CASE 221D-02 **TO-220 TYPE ISSUE D**

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How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



